N-Channel Enhancement Mode Power MOSFET

Description

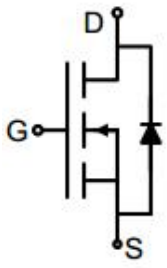
The G08N03D2 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge. It can be used in a wide variety of applications.

General Features

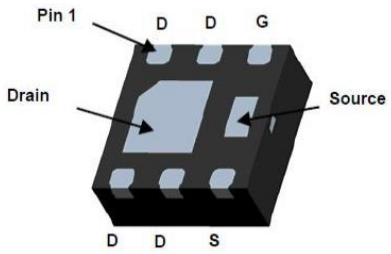
- V_{DS} 30V
- I_D (at V_{GS} = 10V) 8A
- $R_{DS(ON)}$ (at V_{GS} = 10V) < 19mΩ
- $R_{DS(ON)}$ (at V_{GS} = 4.5V) < 25mΩ
- 100% Avalanche Tested
- RoHS Compliant

Application

- Power switch
- DC/DC converters



Schematic diagram



DFN2x2-6L

Ordering Information

Device	Package	Marking	Packaging
G08N03D2	DFN2x2-6L	G08N03	3000pcs/Reel

Absolute Maximum Ratings T_C = 25ºC, unless otherwise noted

Parameter		Symbol	Value	Unit
Drain-Source Voltage		V_{DS}	30	V
Continuous Drain Current	T_C = 25ºC	I_D	8	A
	T_C = 100ºC		5	
Pulsed Drain Current (note1)		I_{DM}	32	A
Gate-Source Voltage		V_{GS}	±20	V
Power Dissipation		P_D	17	W
Single pulse avalanche energy （note2）		E_{AS}	12	mJ
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 To 150	ºC

Thermal Resistance

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Ambient, t≤10s	R_{thJA}	7.35	ºC/W

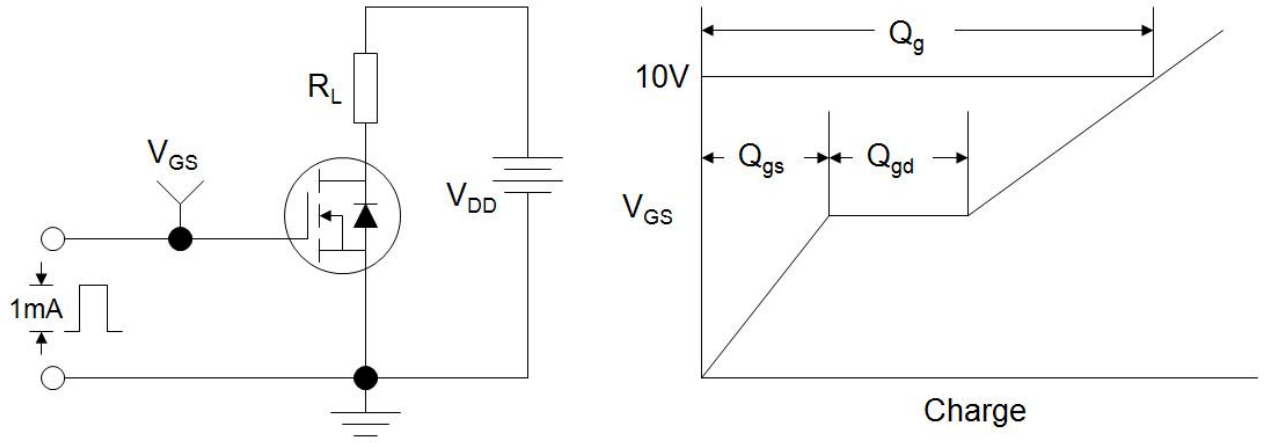
Specifications T_J = 25ºC, unless otherwise noted

Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static Parameters						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 250μA	30	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 30V, V_{GS} = 0V	--	--	1	μA
Gate-Source Leakage	I_{GSS}	V_{GS} = ±20V	--	--	±100	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	1.0	1.45	2.0	V
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS} = 10V, I_D = 3A	--	17	19	mΩ
		V_{GS} = 4.5V, I_D = 3A	--	22	25	
Forward Transconductance	g_{FS}	V_{GS} = 5V, I_D = 3A	--	7	--	S
Dynamic Parameters						
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = 15V, f = 1.0MHz	--	570	--	pF
Output Capacitance	C_{oss}		--	62	--	
Reverse Transfer Capacitance	C_{rss}		--	54	--	
Total Gate Charge	Q_g	V_{DD} = 15V, I_D = 3A, V_{GS} = 10V	--	16	--	nC
Gate-Source Charge	Q_{gs}		--	2	--	
Gate-Drain Charge	Q_{gd}		--	1.8	--	
Turn-on Delay Time	$t_{d(on)}$	V_{DD} = 15V, I_D = 3A, R_G = 3Ω	--	4	--	ns
Turn-on Rise Time	t_r		--	26	--	
Turn-off Delay Time	$t_{d(off)}$		--	15	--	
Turn-off Fall Time	t_f		--	24	--	
Drain-Source Body Diode Characteristics						
Continuous Body Diode Current	I_S	T_C = 25ºC	--	--	8	A
Body Diode Voltage	V_{SD}	T_J = 25ºC, I_{SD} = 3A, V_{GS} = 0V	--	--	1.2	V
Reverse Recovery Charge	Qrr	I_F = 3A, V_{GS} = 0V di/dt=100A/us	--	1	--	nC
Reverse Recovery Time	Trr		--	12	--	ns

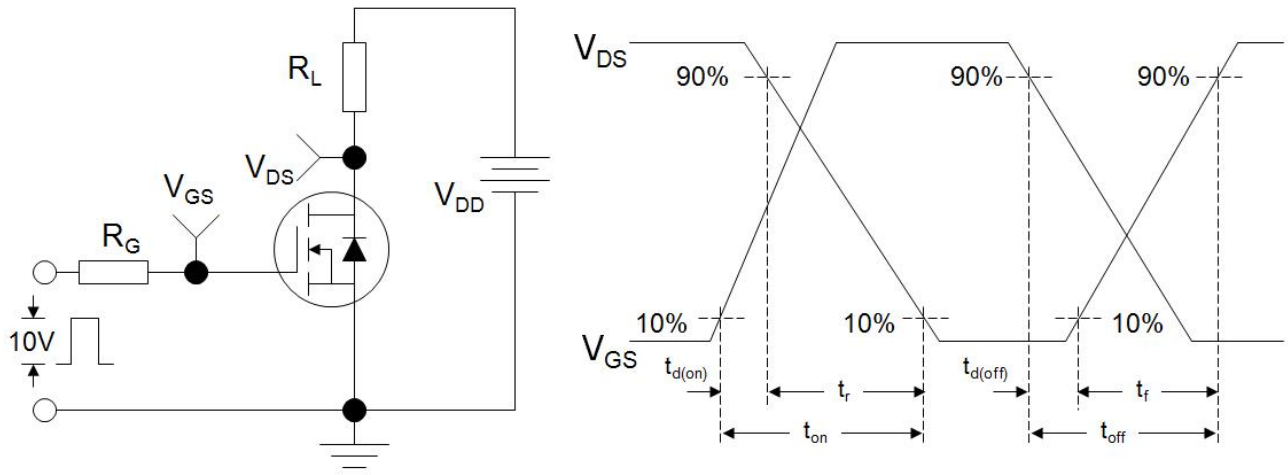
Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. EAS condition : Tj=25℃ ,VDD=30V,VGS=10V,L=0.5mH,Rg=25Ω
   The table shows the minimum avalanche energy, which is 30mJ when the device is tested until failure
3. Identical low side and high side switch with identical R_G

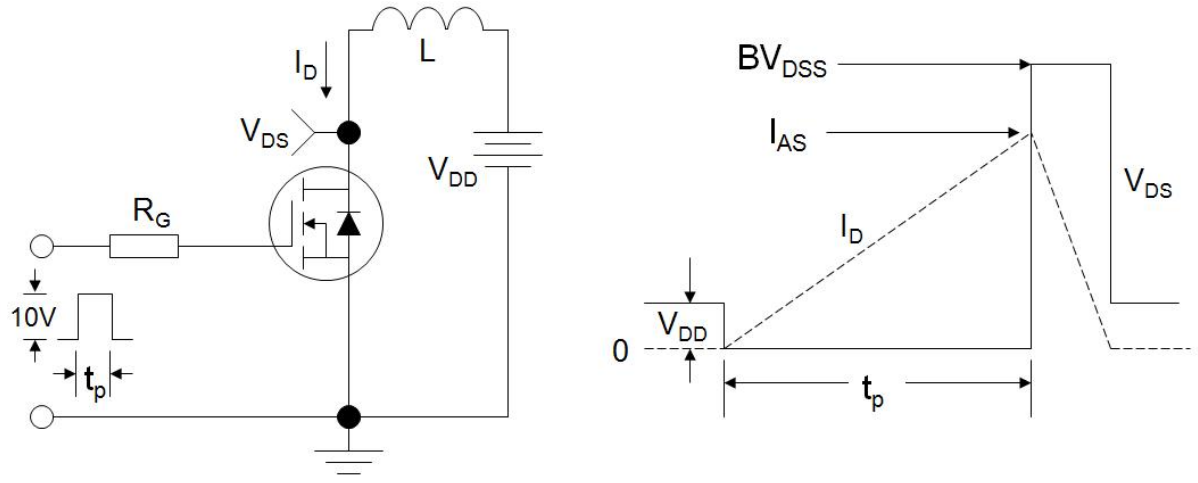
Gate Charge Test Circuit



Switch Time Test Circuit



EAS Test Circuit



Typical Characteristics T_J = 25ºC, unless otherwise noted

Figure 1. Output Characteristics

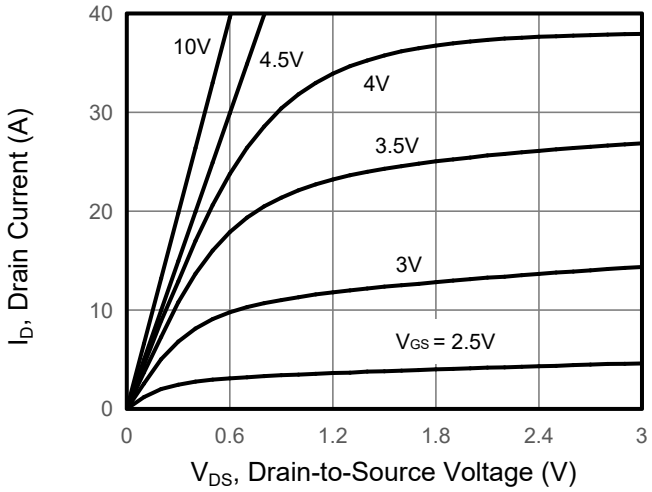


Figure 2. Transfer Characteristics

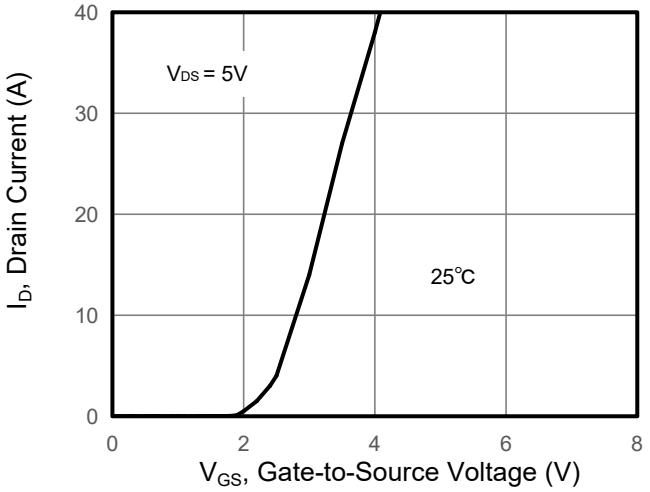


Figure 3. Drain Source On Resistance

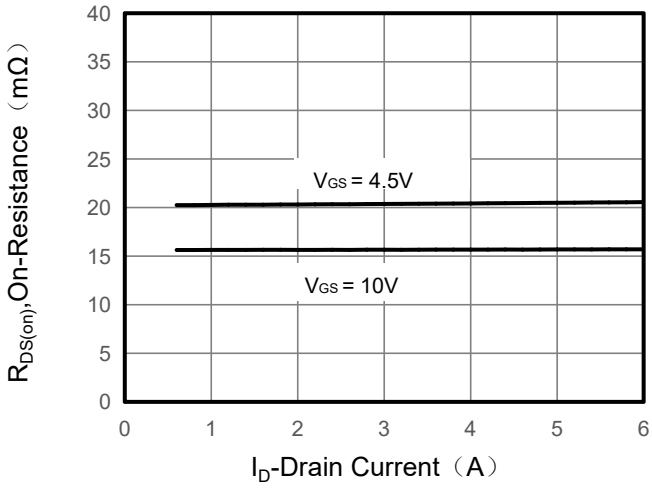


Figure 4. Gate Charge

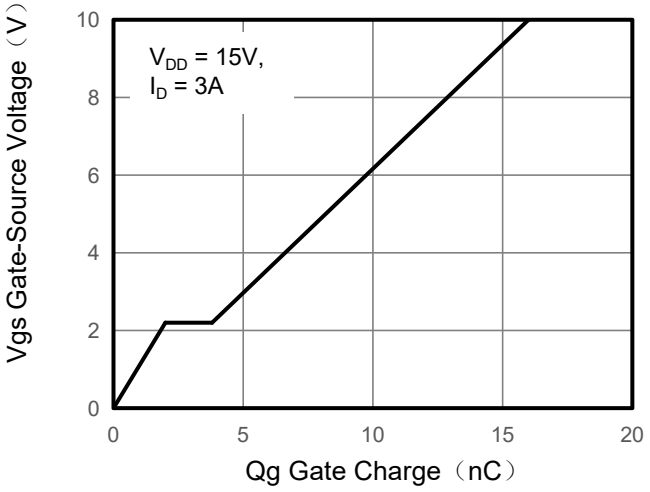


Figure 5. Capacitance

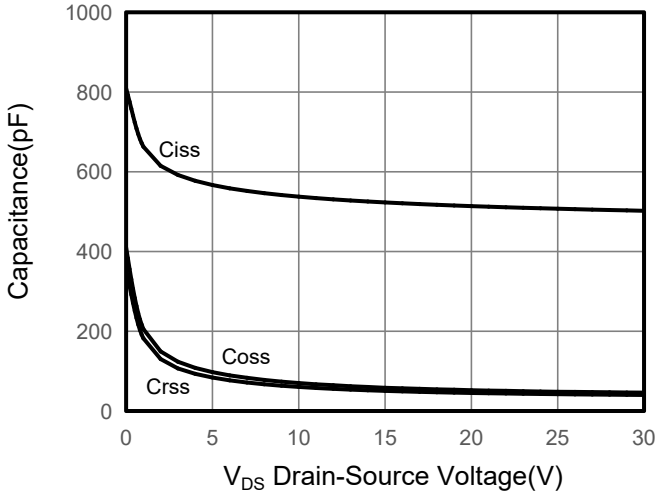
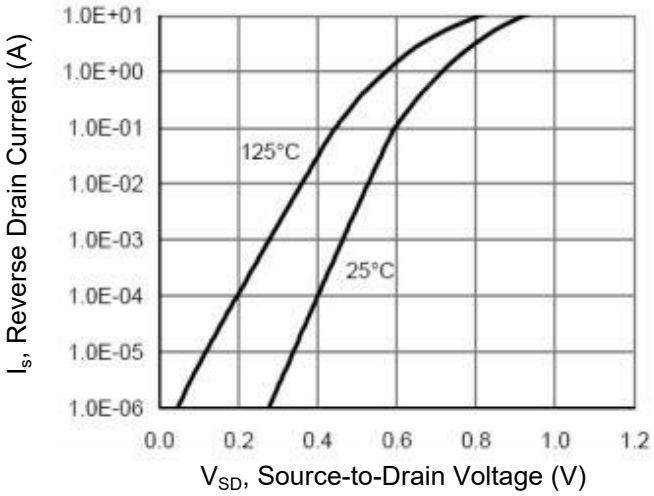


Figure 6. Source-Drain Diode Forward



Typical Characteristics T_J = 25ºC, unless otherwise noted

Figure 7. Drain-Source On-Resistance

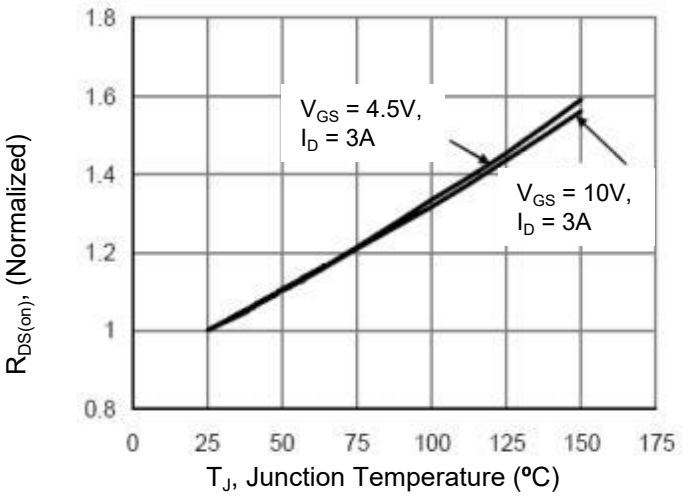


Figure 8. Safe Operation Area

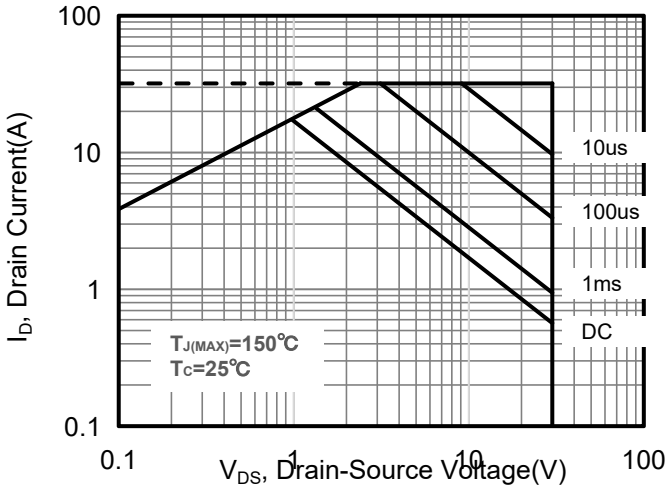


Figure 9. Maximum Continuous Drain Current vs Case Temperature

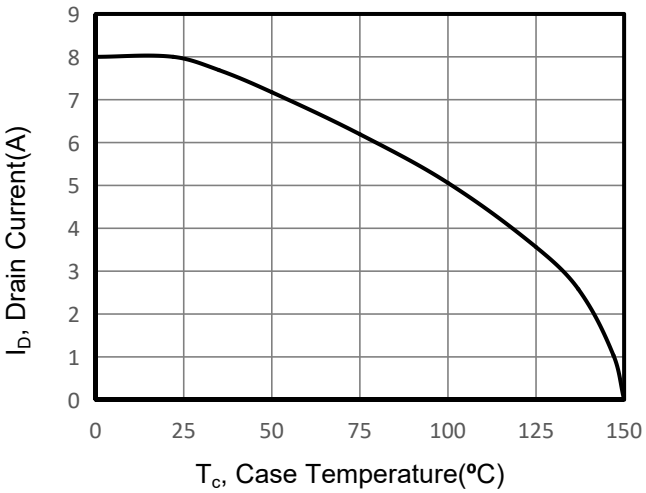
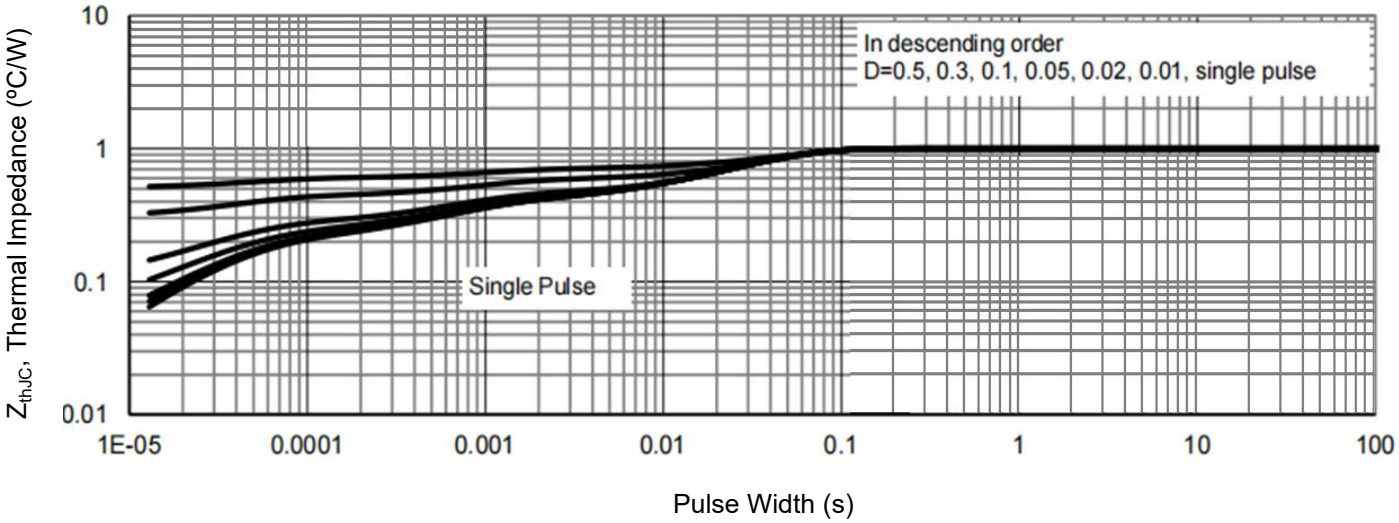
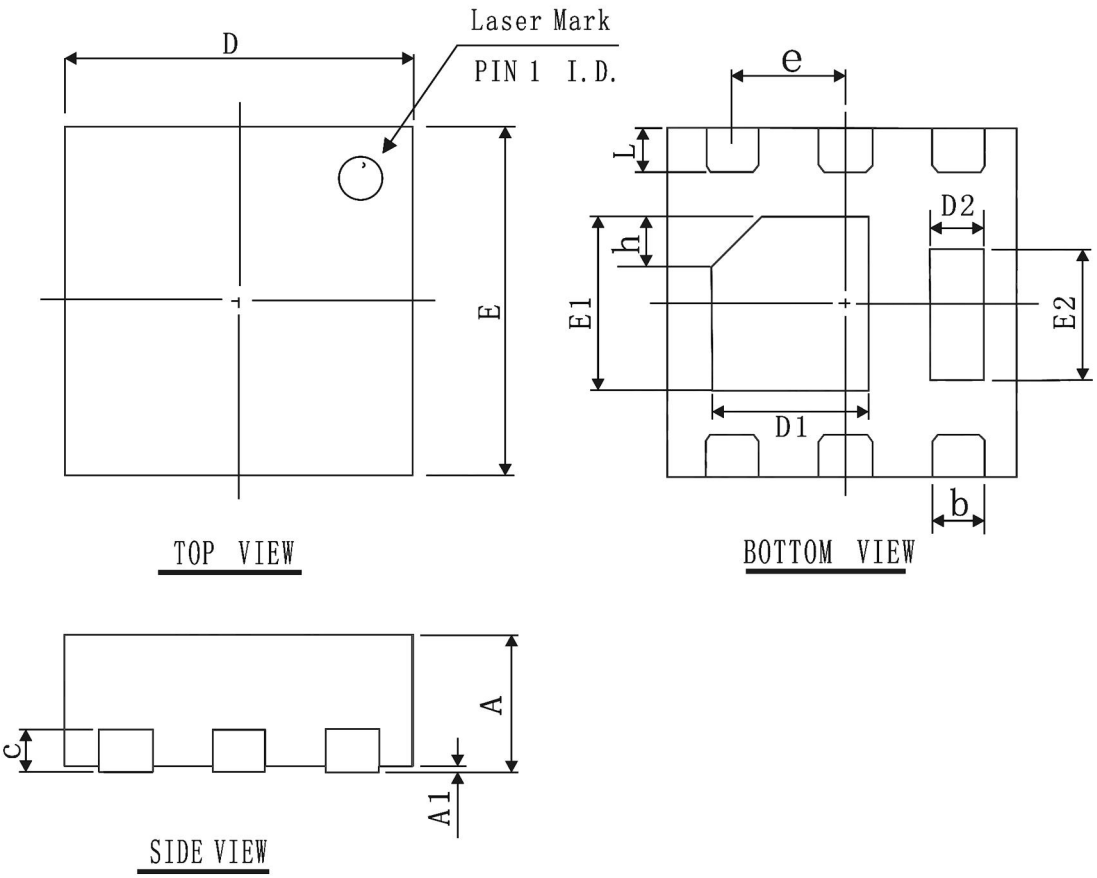


Figure 10. Normalized Maximum Transient Thermal Impedance



DFN2x2-6L Package Information



COMMON DIMENSIONS
(UNITS OF MEASURE=mm)

SYMBOL	MIN	NOM	MAX
A	0.70	0.75	0.80
A1	0.00	0.02	0.05
b	0.20	0.25	0.30
D	1.95	2.00	2.07
E	1.95	2.00	2.07
D1	0.80	0.90	1.00
E1	0.90	1.00	1.10
D2	0.20	0.30	0.40
E2	0.65	0.75	0.85
L	0.20	0.25	0.35
h	0.20	0.25	0.30
c	0.203 REF		
e	0.65 BSC		

其它厚度尺寸如下

A	0.55	0.60	0.65